

Sensitive and standard 8 A SCRs

Datasheet - production data

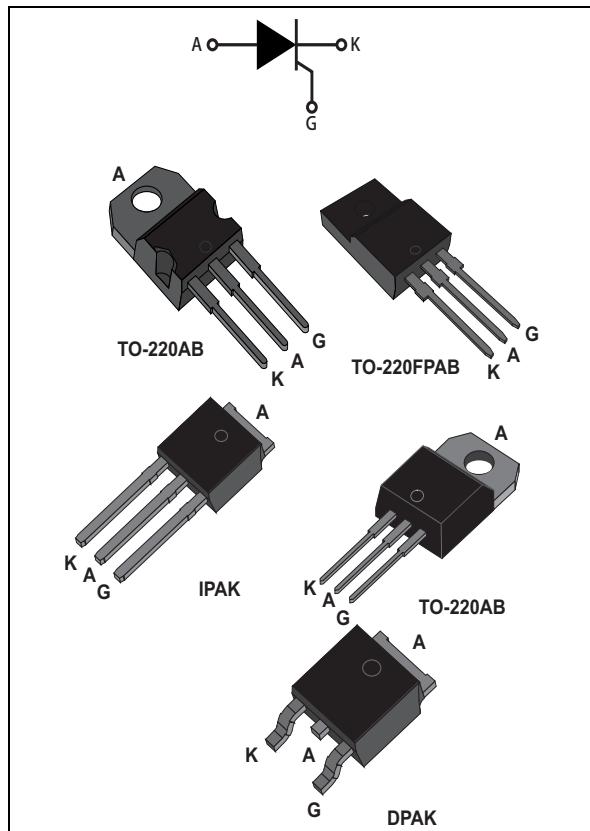
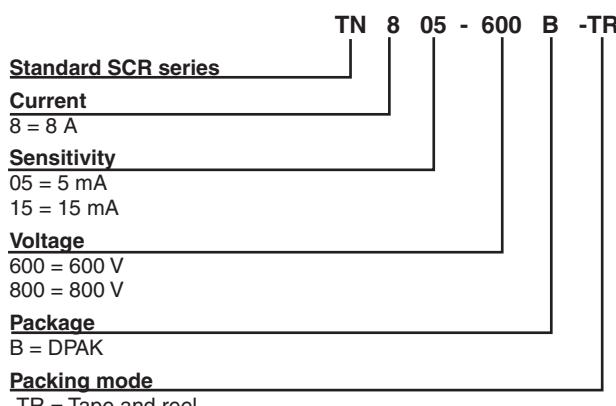


Figure 1. TN8 series



Description

Available either in sensitive (TS8) or standard (TN8 / TYN) gate triggering levels, the 8 A SCR series is suitable to fit all modes of control found in applications such as overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, inrush current limiting circuits, capacitive discharge ignition and voltage regulation circuits.

Available in through-hole or surface-mount packages, they provide an optimized performance in a limited space.

Features

- On-state rms current, $I_{T(RMS)}$ 8 A
- Repetitive peak off-state voltage, V_{DRM}/V_{RRM} 600 and 800 V
- Triggering gate current, I_{GT} 0.2 to 15 mA

Figure 2. TS8 series

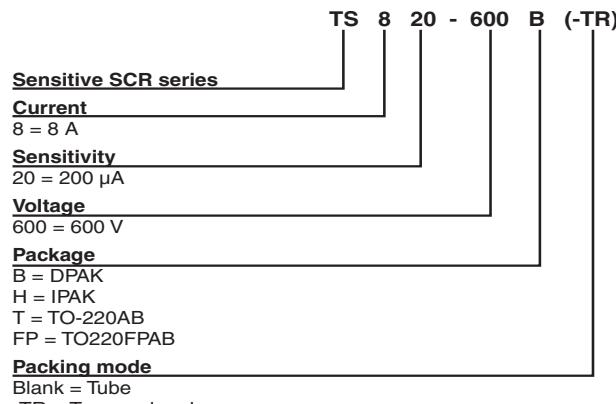
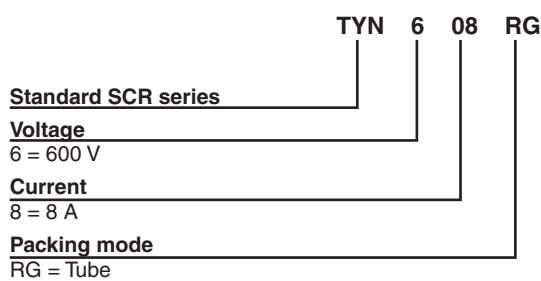


Figure 3. TYNx08 series



1 Characteristics

Table 1. Absolute ratings (limiting values)

Symbol	Parameter	Value			Unit
		TN805	TN815	TYN608	
I _{T(RMS)}	On-state rms current (180° conduction angle)	T _c = 110 °C T0-220FPAB, T _c = 91 °C	8	A	
I _{T(AV)}	Average on-state current (180° conduction angle)	T _c = 110 °C T0-220FPAB, T _c = 91 °C			
I _{TSM}	Non repetitive surge peak on-state current	t _p = 8.3 ms	T _j = 25 °C	73	100
		t _p = 10 ms		70	95
I ² t	I ² t value for fusing	t _p = 10 ms	T _j = 25 °C	24.5	A ² S
dl/dt	Critical rate of rise of on-state current I _G = 2 x I _{GT} , t _r ≤ 100 ns	F = 60 Hz	T _j = 125 °C	50	A/μs
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 125 °C	4	A
P _{G(AV)}	Average gate power dissipation		T _j = 125 °C	1	W
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C
V _{RGM}	Maximum peak reverse gate voltage (for TN8x5 and TYN608 only)			5	V

Table 2. Sensitive electrical characteristics (T_j = 25 °C, unless otherwise specified)

Symbol	Test conditions		TS820	Unit
I _{GT}	V _D = 12 V, R _L = 140 Ω	MAX.	200	μA
V _{GT}		MAX.	0.8	V
V _{GD}	V _D = V _{DRM} , R _L = 3.3 kΩ, R _{GK} = 220 Ω	T _j = 125 °C	MIN.	0.1
V _{RG}	I _{RG} = 10 μA		MIN.	8
I _H	I _T = 50 mA, R _{GK} = 1 kΩ		MAX.	5
I _L	I _G = 1 mA, R _{GK} = 1 kΩ		MAX.	6
dV/dt	V _D = 65% V _{DRM} , R _{GK} = 220 Ω	T _j = 125 °C	MIN.	5
V _{TM}	I _{TM} = 16 A, t _p = 380 μs	T _j = 25 °C	MAX.	1.6
V _{t0}	Threshold voltage	T _j = 125 °C	MAX.	0.85
R _d	Dynamic resistance	T _j = 125 °C	MAX.	46
I _{DRM} I _{RRM}	V _{DRM} = V _{RRM} , R _{GK} = 220 Ω	T _j = 25 °C	MAX.	5
		T _j = 125 °C		1

Table 3. Standard electrical characteristics ($T_j = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test conditions		TN805	TN815	TYN608	Unit
I_{GT}	$V_D = 12\text{ V}$, $R_L = 33\Omega$		MIN.	0.5	2	2
			MAX.	5	15	15
V_{GT}			MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3\text{ k}\Omega$	$T_j = 125^\circ\text{C}$	MIN.	0.2		V
I_H	$I_T = 100\text{ mA}$, gate open		MAX.	25	40	30
I_L	$I_G = 1.2 I_{GT}$		MAX.	30	50	70
dV/dt	$V_D = 67\% V_{DRM}$, gate open	$T_j = 125^\circ\text{C}$	MIN.	50	150	150
V_{TM}	$I_{TM} = 16\text{ A}$, $t_p = 380\mu\text{s}$	$T_j = 25^\circ\text{C}$	MAX.	1.6		V
V_{t0}	Threshold voltage	$T_j = 125^\circ\text{C}$	MAX.	0.85		V
R_d	Dynamic resistance	$T_j = 125^\circ\text{C}$	MAX.	46		$\text{m}\Omega$
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM}$		$T_j = 25^\circ\text{C}$	5		μA
			$T_j = 125^\circ\text{C}$	2		mA

Table4. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	DPAK, IPAK, TO-220AB	1.3
		TO-220FPAB	4.6
$R_{th(j-a)}$	Junction to ambient (DC) $S^{(1)} = 0.5\text{ cm}^2$	DPAK	70
		IPAK	100
		TO-220AB, TO-220FPAB	60
			$^\circ\text{C/W}$

1. S = Copper surface under tab

Figure 4. Maximum average power dissipation versus average on-state current

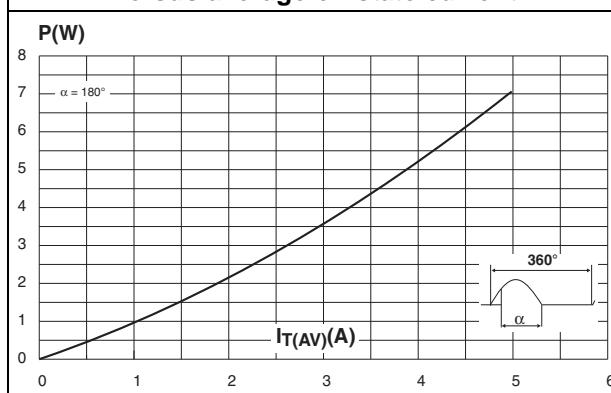


Figure 5. Average and DC on-state current versus case temperature

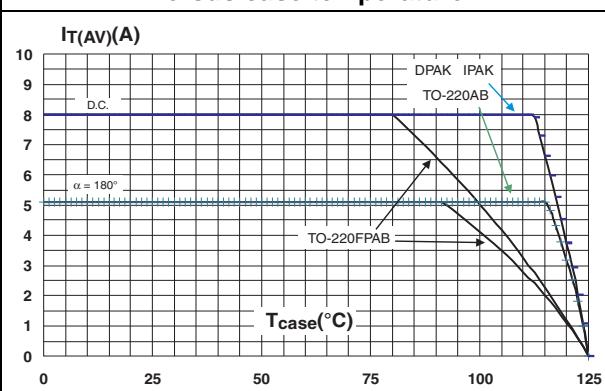


Figure 6. Average and DC on-state current versus ambient temperature

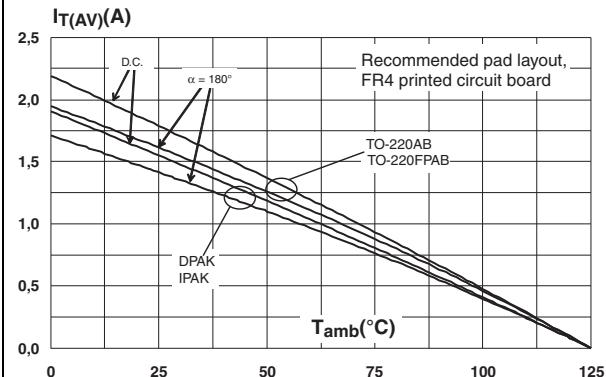


Figure 7. Relative variation of thermal impedance junction to case versus pulse duration

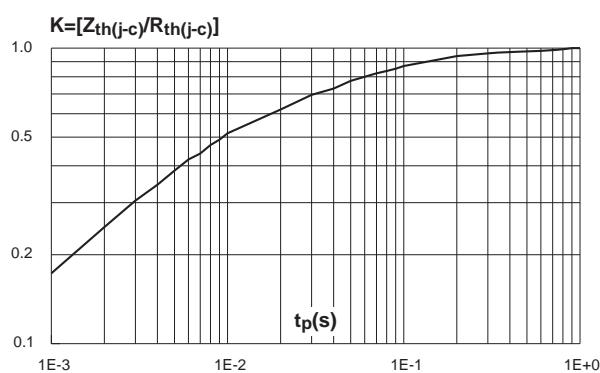


Figure 8. Relative variation of thermal impedance junction to ambient versus pulse duration

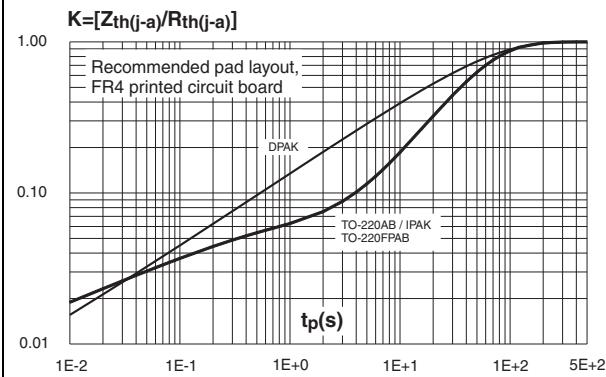


Figure 9. Relative variation of gate trigger current and holding current versus junction temperature for TS820

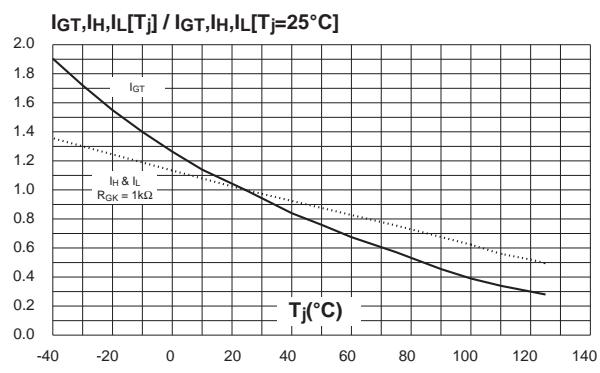


Figure 10. Relative variation of gate trigger and holding current versus junction

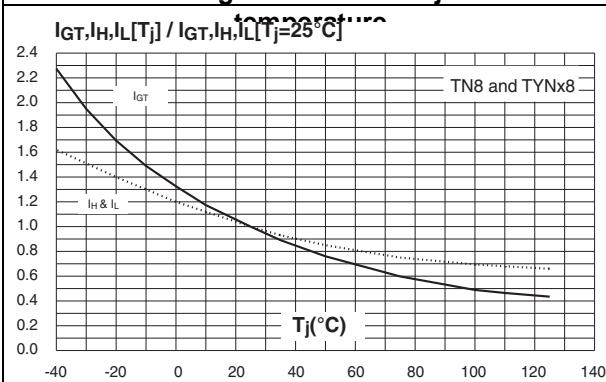


Figure 11. Relative variation of holding current versus gate-cathode resistance (typical values)

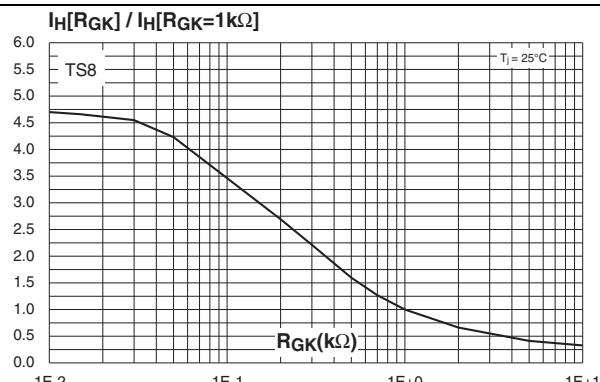


Figure 12. Relative variation of dV/dt immunity versus gate-cathode resistance (typical values) for TS820

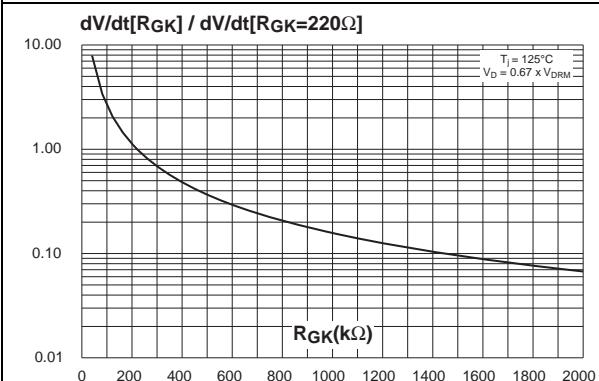


Figure 13. Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values) for TS820

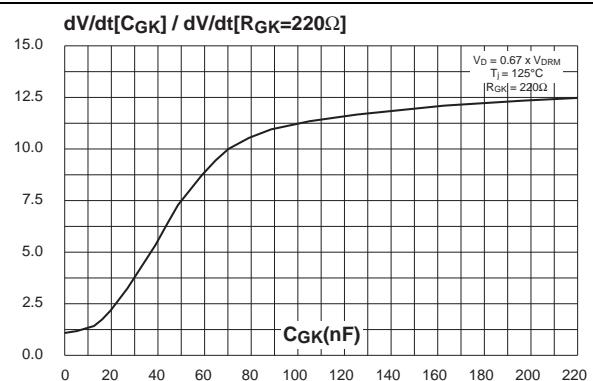


Figure 14. Surge peak on-state current versus number of cycles

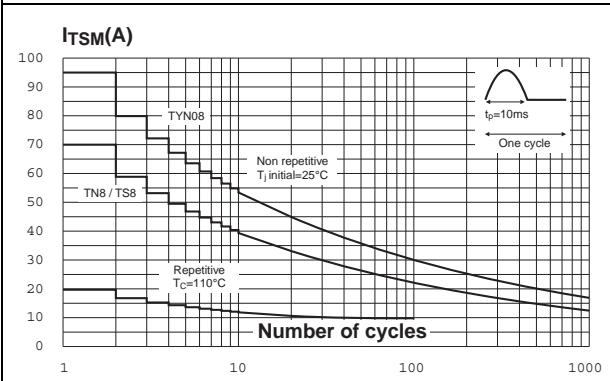


Figure 15. Non-repetitive surge peak on-state current and corresponding values of I^2t

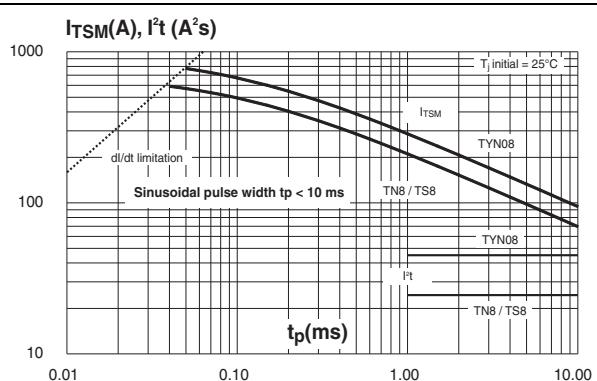


Figure 16. On-state characteristics (maximum values)

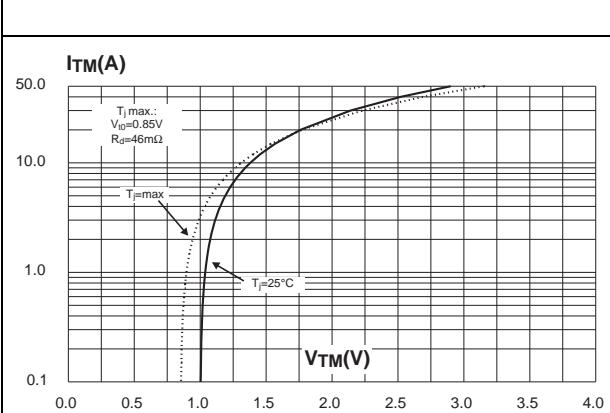
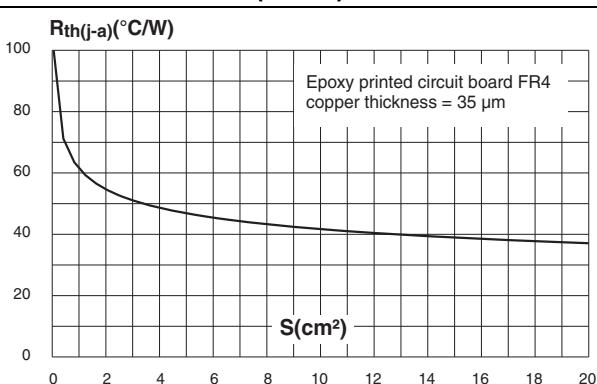


Figure 17. Thermal resistance junction to ambient versus copper surface under tab (DPAK)



2 Package information

- Lead-free packages
- Recommended torque: 0.4 to 0.6 N·m

Figure 18. DPAK dimension definitions

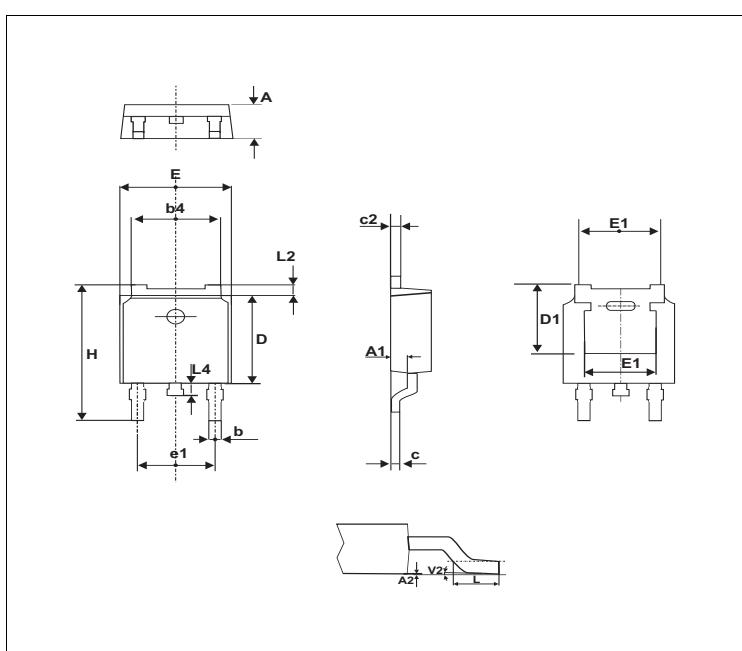
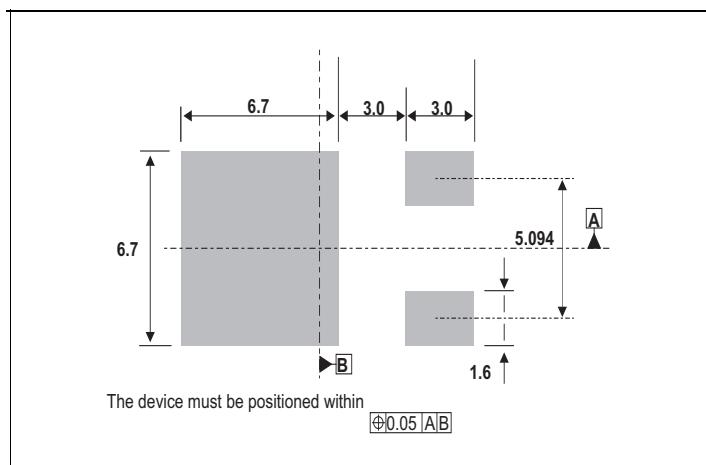


Table 5. DPAK dimension values

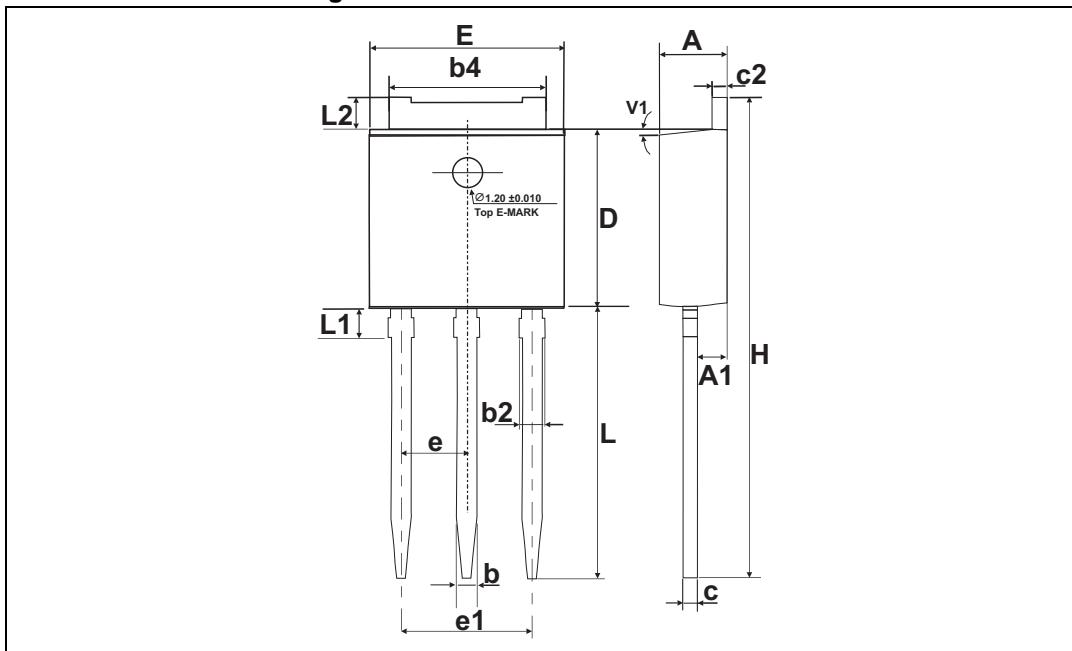
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.18		2.40	0.086		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
b	0.64		0.90	0.025		0.035
b4	4.95		5.46	0.195		0.215
c	0.46		0.61	0.018		0.024
c2	0.46		0.60	0.018		0.023
D	5.97		6.22	0.235		0.244
D1	5.10			0.201		
E	6.35		6.73	0.250		0.264
E1		4.32			0.170	
e1	4.40		4.70	0.173		0.185
H	9.35		10.40	0.368		0.409
L	1.00		1.78	0.039		0.070
L2			1.27			0.05
L4	0.60		1.02	0.023		0.040
V2	0°		8°	0°		8°

Figure 19. Footprint (dimensions in mm)



Note: this package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Figure 20. IPAK dimension definitions



Note: this package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Table 6. IPAK dimension values

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.094
A1	0.90		1.10	0.035		0.043
b	0.64		0.90	0.025		0.035
b2			0.95			0.037
b4	5.20		5.43	0.204		0.213
c	0.45		0.60	0.017		0.023
c2	0.46		0.60	0.018		0.023
D	6		6.20	0.236		0.244
E	6.40		6.70	0.252		0.263
e		2.28			0.090	
e1	4.40		4.60	0.173		0.181
H		16.10			0.634	
L	9		9.60	0.354		0.377
L1	0.8		1.20	0.031		0.047

Table 7. IPAK dimension values

L2		0.80	1.25		0.031	0.049
V1		10°			10°	

Figure 21. TO-220AB dimension definitions

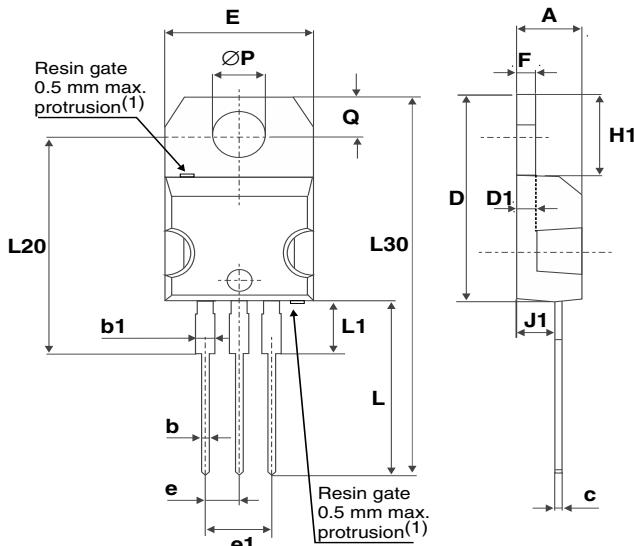


Table 8. TO-220AB dimension values

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.17	0.18
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.045	0.067
c	0.48	0.70	0.019	0.027
D	15.25	15.75	0.60	0.62
D1	1.27 typ.		0.05 typ.	
E	10	10.40	0.39	0.41
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.19	0.20
F	1.23	1.32	0.048	0.052
H1	6.20	6.60	0.24	0.26
J1	2.40	2.72	0.094	0.107
L	13	14	0.51	0.55
L1	3.50	3.93	0.137	0.154
L20	16.40 typ.		0.64 typ.	
L30	28.90 typ.		1.13 typ.	
ØP	3.75	3.85	0.147	0.151
Q	2.65	2.95	0.104	0.116

Figure 22. TO-220AB (NIns. & Ins. 20-up) dimension definitions

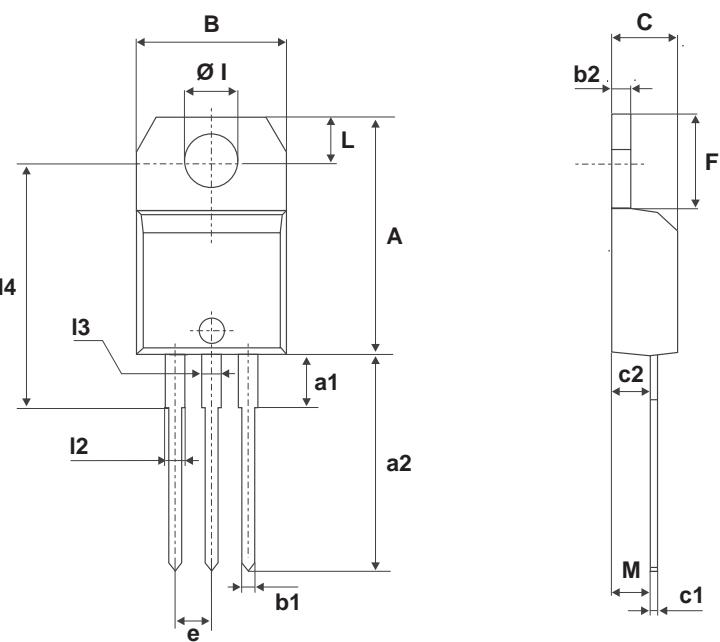


Table9. TO-220AB (NIns. & Ins. 20-up) dimension values

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
ØI	3.75		3.85	0.147		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
I3	1.14		1.70	0.044		0.066
M		2.60			0.102	

Figure 23. TO-220FPAB dimension definitions

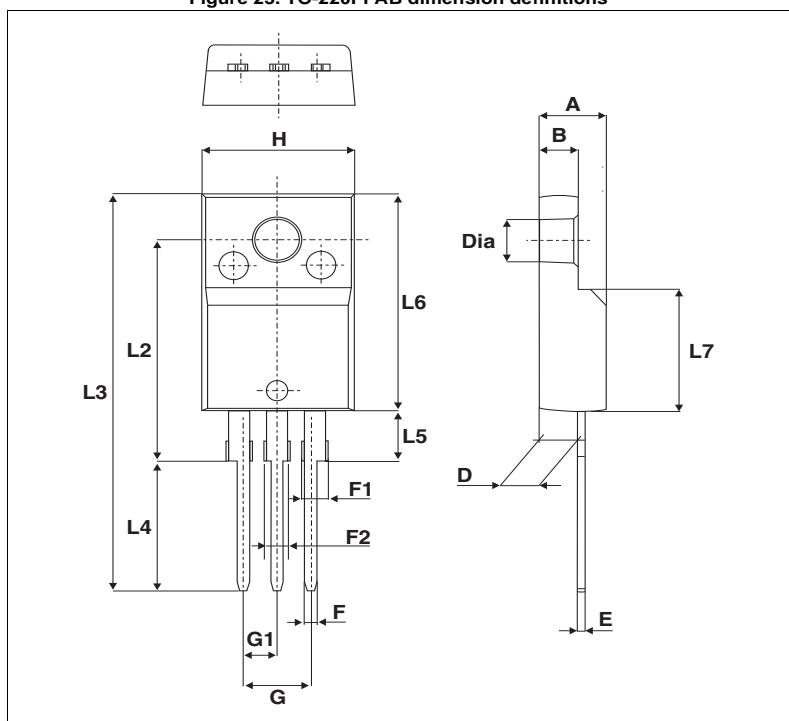


Table 10. TO-220FPAB dimension values

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.70	0.018		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.70	0.045		0.067
F2	1.15		1.70	0.045		0.067
G	4.95		5.20	0.195		0.205
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.63	
L3	28.6		30.6	1.126		1.205
L4	9.8		10.6	0.386		0.417
L5	2.9		3.6	0.114		0.142
L6	15.9		16.4	0.626		0.646
L7	9.00		9.30	0.354		0.366
Dia.	3.00		3.20	0.118		0.126

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